imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

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CREE 🔶 C3D16060D Silicon Carbide Schottky Diode **Z-Rec®** Rectifier

Features

- 600-Volt Schottky Rectifier •
- Zero Reverse Recovery Current ۰
- Zero Forward Recovery Voltage •
- •
- High-Frequency Operation Temperature-Independent Switching Behavior •
- Extremely Fast Switching
- Positive Temperature Coefficient on V_F •

Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency •
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

- Switch Mode Power Supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free Wheeling Diodes in Inverter stages
- AC/DC converters .

Package



V_{RRM}

Q_c

=

=

I_c(T_c=135°C) =

600 V

22 A**

40 nC**



PIN 1O-►



PIN 3O-►

Part Number	Package	Marking
C3D16060D	TO-247-3	C3D16060

Symbol	Parameter	Value	Unit	Test Conditions	Note
V _{RRM}	Repetitive Peak Reverse Voltage	600	V		
V _{RSM}	Surge Peak Reverse Voltage	600	V		
V _{DC}	DC Blocking Voltage	600	V		
I _F	Continuous Forward Current (Per Leg/Device)	23/46 11/22 8/16	A	T _c =25°C T _c =135°C T _c =150°C	Fig. 3
\mathbf{I}_{FRM}	Repetitive Peak Forward Surge Current (Per Leg/Device)	37.5/75 25.5/51	А	$T_c=25^{\circ}C$, $t_p=10$ ms, Half Sine Wave $T_c=110^{\circ}C$, $t_p=10$ ms, Half Sine Wave	
\mathbf{I}_{FSM}	Non-Repetitive Peak Forward Surge Current (Per Leg/Device)	71/142 60/120	A	$T_c = 25^{\circ}C$, $t_p = 10$ ms, Half Sine Wave $T_c = 110^{\circ}C$, $t_p = 10$ ms, Half Sine Wave	Fig. 8
\mathbf{I}_{FSM}	Non-Repetitive Peak Forward Surge Current (Per Leg/Device)	650/1300 530/1080	А	$T_c=25$ °C, $t_p=10 \ \mu$ s, Pulse $T_c=110$ °C, $t_p=10 \ \mu$ s, Pulse	Fig. 8
P_{tot}	Power Dissipation (Per Leg)	100* 43.5*	w	W $T_c = 25^{\circ}C$ $T_c = 110^{\circ}C$	
dV/dt	Diode dV/dt ruggedness	200	V/ns	V _R =0-600V	
∫i²dt	i ² t value (Per Leg)	25 18	A ² s	$T_c = 25^{\circ}C, t_p = 10 \text{ ms}$ $T_c = 110^{\circ}C, t_p = 10 \text{ ms}$	
$T_{_{\mathrm{J}}}$, $T_{_{\mathrm{stg}}}$	Operating Junction and Storage Temperature	-55 to +175	°c		
	TO-247 Mounting Torque	1 8.8	Nm Ibf-in	M3 Screw 6-32 Screw	

* Per Leg, ** Per Device



Electrical Characteristics (Per Leg)

Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
V _F	Forward Voltage	1.5 2.1	1.8 2.4	V	$I_{F} = 8 \text{ A } T_{J} = 25^{\circ}\text{C}$ $I_{F} = 8 \text{ A } T_{J} = 175^{\circ}\text{C}$	Fig. 1
I _R	Reverse Current	8.5 17	42.5 170	μΑ	V _R = 600 V T _J =25°C V _R = 600 V T _J =175°C	Fig. 2
Q _c	Total Capacitive Charge	20		nC	$V_{R} = 600 V, I_{F} = 8A$ $di/dt = 500 A/\mu s$ $T_{J} = 25^{\circ}C$	Fig. 5
С	Total Capacitance	395 37 32		pF	$V_{R} = 0 V, T_{J} = 25^{\circ}C, f = 1 MHz$ $V_{R} = 200 V, T_{J} = 25^{\circ}C, f = 1 MHz$ $V_{R} = 400 V, T_{J} = 25^{\circ}C, f = 1 MHz$	Fig. 6
E _c	Capacitance Stored Energy	3.0		μJ	V _R = 400 V	Fig. 7

Note: This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Тур.	Unit	Note
$R_{_{ ext{ hetaJC}}}$	Thermal Resistance from Junction to Case	1.5 * 0.75 **	°C/W	Fig. 9

* Per Leg, ** Per Device

Typical Performance (Per Leg)

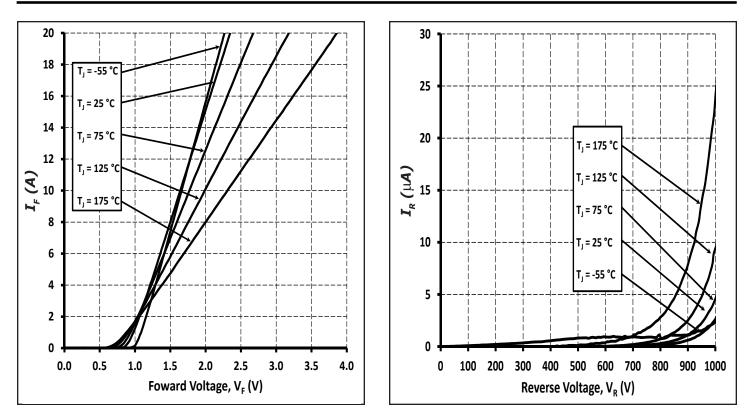
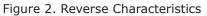
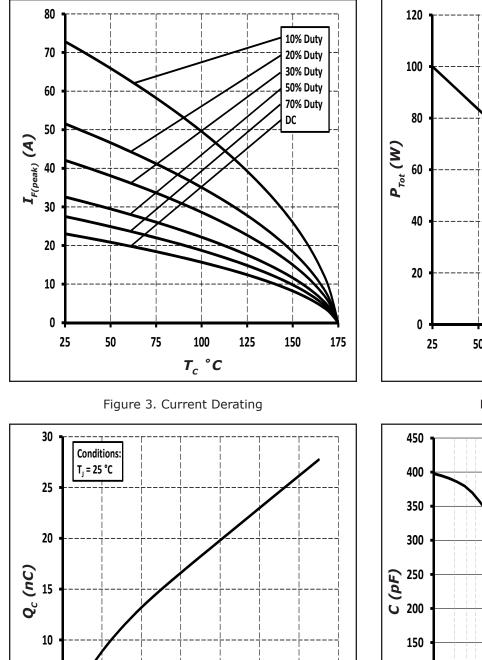


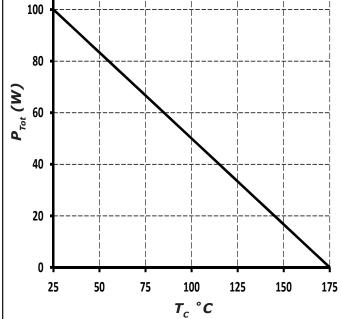
Figure 1. Forward Characteristics

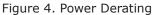




Typical Performance (Per Leg)







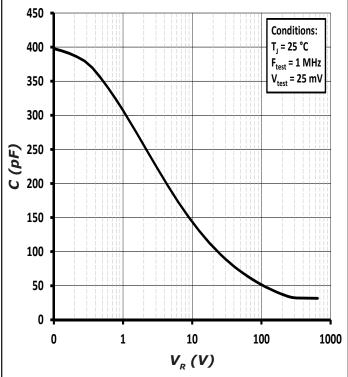
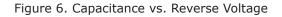


Figure 5. Total Capacitance Charge vs. Reverse Voltage

 $V_{R}(V)$





Typical Performance (Per Leg)

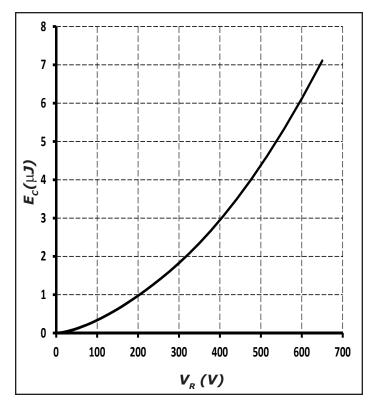


Figure 7. Capacitance Stored Energy

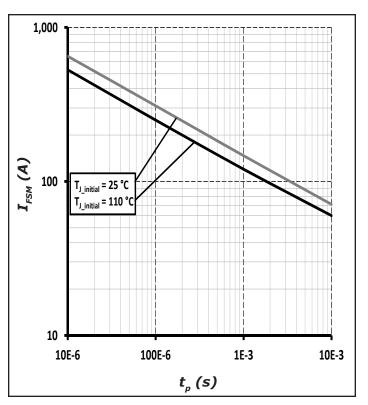


Figure 8. Non-repetitive peak forward surge current versus pulse duration (sinusoidal waveform)

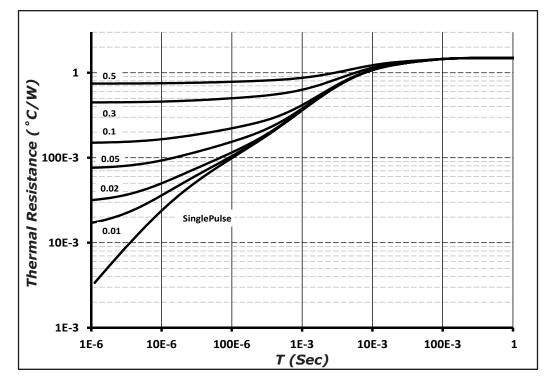


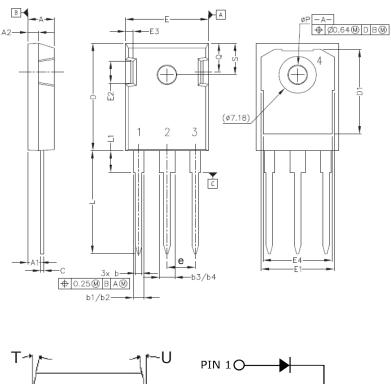
Figure 9. Transient Thermal Impedance

4



Package Dimensions

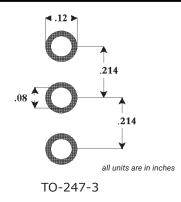
Package TO-247-3





DOG	Inc	hes	Millimeters		
POS	Min	Мах	Min	Мах	
А	.190	.205	4.83	5.21	
A1	.090	.100	2.29	2.54	
A2	.075	.085	1.91	2.16	
b	.042	.052	1.07	1.33	
b1	.075	.095	1.91	2.41	
b2	.075	.085	1.91	2.16	
b3	.113	.133	2.87	3.38	
b4	.113	.123	2.87	3.13	
с	.022	.027	0.55	0.68	
D	.819	.831	20.80	21.10	
D1	.640	.695	16.25	17.65	
D2	.037	.049	0.95	1.25	
E	.620	.635	15.75	16.13	
E1	.516	.557	13.10	14.15	
E2	.145	.201	3.68	5.10	
E3	.039	.075	1.00	1.90	
E4	.487	.529	12.38	13.43	
е	.214	BSC	5.44 BSC		
Ν		3	3		
L	.780	.800	19.81	20.32	
L1	.161	.173	4.10	4.40	
ØP	.138	.144	3.51	3.65	
Q	.216	.236	5.49	6.00	
S	.238	.248	6.04	6.30	
Т	9°	11°	9°	11°	
U	9°	11°	9°	11°	
V	2°	8°	2°	8°	
W	2°	8°	2°	8°	

Recommended Solder Pad Layout



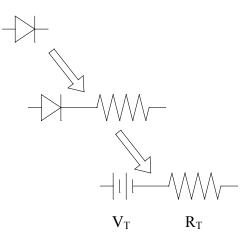
Part Number	Package	Marking
C3D16060D	TO-247-3	C3D16060

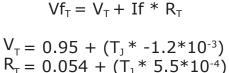
Note: Recommended soldering profiles can be found in the applications note here: http://www.wolfspeed.com/power_app_notes/soldering





Diode Model (Per Leg)





Note: T_j = Diode Junction Temperature In Degrees Celsius, valid from 25°C to 175°C

Notes

• RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented January 2, 2013. RoHS Declarations for this product can be obtained from your Wolfpseed representative or from the Product Ecology section of our website at http://www.wolfspeed.com/Power/Tools-and-Support/Product-Ecology.

• **REACh Compliance**

REACh substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact a Cree representative to insure you get the most up-to-date REACh SVHC Declaration. REACh banned substance information (REACh Article 67) is also available upon request.

This product has not been designed or tested for use in, and is not intended for use in, applications implanted into
the human body nor in applications in which failure of the product could lead to death, personal injury or property
damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines,
cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control
systems, or air traffic control systems.

Related Links

- Cree SiC Schottky diode portfolio: http://www.wolfspeed.com/Power/Products#SiCSchottkyDiodes
- Schottky diode Spice models: http://www.wolfspeed.com/power/tools-and-support/DIODE-model-request2
- SiC MOSFET and diode reference designs: http://go.pardot.com/l/101562/2015-07-31/349i

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